

2020년 2월 13일(목), 09:00~10:30

Room A (에메랄드 I, 5층)

E. Compound Semiconductors 분과

[TA1-E] Compound Semiconductor Technology I

<p>TA1-E-1 09:00~09:15</p>	<p><b>AlGaN/GaN/AlN Double-hetero Structure High Electron Mobility Transistors Grown by HT-MOCVD</b> Uiho Choi, Donghyeop Jung, Minho Kim, Taehoon Jang, Yongjun Nam, Byeongchan So, Taemyung Kwak, and Okhyun Nam <i>Department of Nano-Optical Engineering, Korea Polytechnic University</i></p>
<p>TA1-E-2 09:15~09:30</p>	<p><b>Effective Current Collapse Reduction in GaN-based MISHFETs with Al<sub>2</sub>O<sub>3</sub>/AlN Passivation Layer</b> Jun-Hyeok Lee, M. Siva Pratap Reddy, Jeong-Gil Kim, Woo-Hyun Ahn, and Jung-Hee Lee <i>School of Electronics Engineering, Kyungpook National University</i></p>
<p>TA1-E-3 09:30~09:45</p>	<p><b>P-GaN 게이트 기반 AlGaN/GaN E-mode FET 제작을 위한 선택적 식각 공정 개발</b> Won-Ho Jang, Hyun-Seop Kim, Dac Duc Chu, and Ho-Young Cha <i>School of Electrical and Electronic Engineering, Hongik University</i></p>
<p>TA1-E-4 09:45~10:00</p>	<p><b>Leakage Reduction and Mobility Enhancement in InGaSb p-FET</b> SangHyeon Kim<sup>1</sup>, Ilpyo Roh<sup>2,3</sup>, JaeHoon Han<sup>2</sup>, Dae-Myeong Geum<sup>1</sup>, Seong Kwang Kim<sup>1</sup>, Sooseok Kang<sup>2</sup>, Hang-Kyu Kang<sup>2</sup>, Woo Chul Lee<sup>2</sup>, Seong Keun Kim<sup>2</sup>, Do Kyung Hwang<sup>2</sup>, Yun Heub Song<sup>3</sup>, and Jindong Song<sup>2</sup> <sup>1</sup>KAIST, <sup>2</sup>KIST, <sup>3</sup>Department of Electronics and Communications Engineering, Hanyang University</p>
<p>TA1-E-5 10:00~10:15</p>	<p><b>Remote Epitaxy of GaN Microrod Heterostructures for Deformable Light-emitting Diodes and Substrate Recycle</b> Junseok Jeong, Dae Kwon Jin, and Young Joon Hong <i>Sejong University</i></p>
<p>TA1-E-6 10:15~10:30</p>	<p><b>Epitaxial BeO Dielectric Based AlGaN/GaN Metal-oxide Semiconductor High-electron-mobility Transistors</b> Dohwan Jung<sup>1,2</sup>, Seonno Yoon<sup>1,2</sup>, and Jungwoo Oh<sup>1,2</sup> <sup>1</sup>School of Integrated Technology, Yonsei University, <sup>2</sup>Yonsei Institute of Convergence Technology</p>